To all our customers

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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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## 2SA1390

## Silicon PNP Epitaxial



ADE-208-1017 (Z) 1st. Edition Mar. 2001

#### Application

Low frequency amplifier



### 2SA1390

#### **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-35	V
Collector to emitter voltage	V <sub>CEO</sub>	-35	V
Emitter to base voltage	V <sub>EBO</sub>	-4	V
Collector current	Ι <sub>c</sub>	-500	mA
Collector power dissipation	Pc	300	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

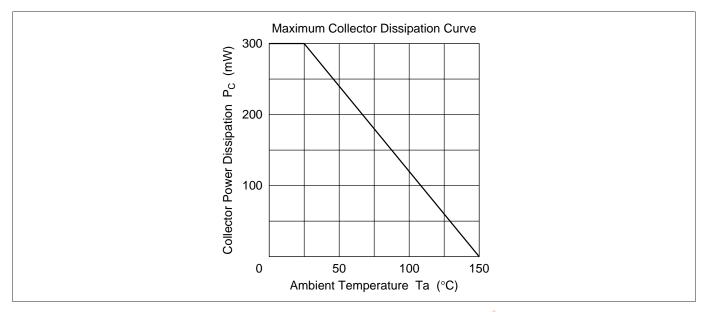
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#### **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-35	_	_	V	$I_{c} = -10 \ \mu A, I_{E} = 0$
Collector to emitter breakdown voltage	N V <sub>(BR)CEO</sub>	-35	-	5	V	$I_c = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-4	-	3	V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I <sub>CBO</sub>	-/		-0.5	μΑ	$V_{\rm CB} = -20$ V, $I_{\rm E} = 0$
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	-	-0.2	-0.6	V	$I_{c} = -150 \text{ mA}, I_{B} = -15 \text{ mA}^{*2}$
DC current transfer ratio	h <sub>FE1</sub> *1	60	—	320		$V_{ce} = -3 \text{ V}, \text{ I}_{c} = -10 \text{ mA}$
DC current transfer ratio	h <sub>FE2</sub>	10		—		$V_{ce} = -3 \text{ V}, \text{ I}_{c} = -500 \text{ mA}^{*2}$
Base to emitter voltage	V <sub>BE</sub>		-0.64	—	V	$V_{ce} = -3 \text{ V}, \text{ I}_{c} = -10 \text{ mA}$
Notes: 1. The 2SA1390 is gr	ouped by h	FE1 as fol	lows.			
2. Pulse test						
B C I	0					
60 to 120 100 to 200 1	60 to 320					

See characteristic curves of 2SA673.





### 2SA1390

#### **Package Dimensions**

4.2 Max	2.2 Max	As of January, 2001 Unit: mm
1.8 Max		
	0.4 ± 0.1	U U
	J.C	
1.27 1.27	Hitachi Code JEDEC	SPAK
	EIAJ Mass (reference value	—



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